

ABSTRACT

The present invention provides a wafer polishing method and a polishing apparatus which are capable of preventing peripheral sags of a wafer due to polishing and then manufacturing the wafer, especially an SOI wafer at a high flatness level. There is provided a wafer polishing method using a polishing apparatus which comprises a rotatable table having a polishing cloth adhered thereon and a polishing head equipped with a wafer holding plate opposing to the table and in which the back surface of the wafer is held by a holding surface of the wafer holding plate and the front surface of the wafer is pressed to and polished by the polishing pad, comprising a polishing step of polishing the front surface of the wafer to a predetermined total polishing stock removal without changing the polishing apparatus, wherein the polishing step is divided into plural sub-steps and a holding position of the wafer in a subsequent sub-step is different from a holding position of the wafer in a previous sub-step.

(19) 世界知的所有権機関
国際事務局



Rec'd PCT/PTO

08 FEB 2005



(43) 国際公開日
2004 年 2 月 19 日 (19.02.2004)

PCT

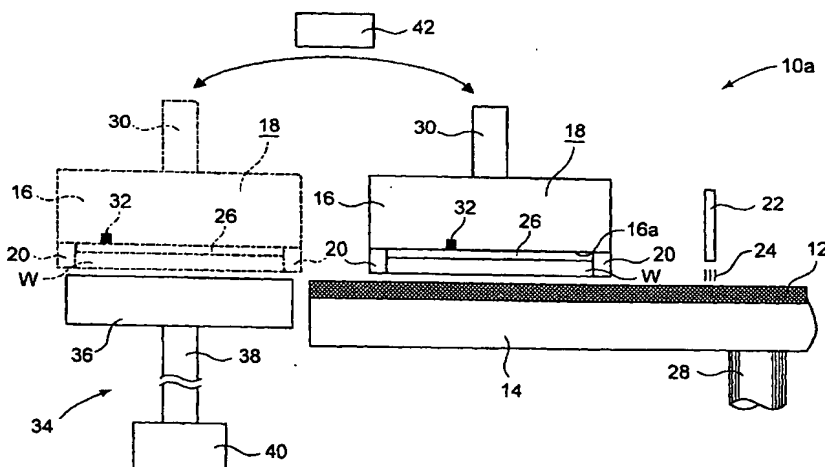
(10) 国際公開番号
WO 2004/015752 A1

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NL, PT, RO, SE, SI, SK, TR).

[続葉有]

(54) Title: METHOD AND APPARATUS FOR POLISHING WAFER

(54) 発明の名称: ウェーハの研磨方法及び装置



(57) **Abstract:** A method and apparatus for polishing a wafer, in which method and apparatus face drops caused by polishing is prevented from occurring and which is capable of producing a wafer with high flatness, particularly, a SOI wafer. The polishing method uses a polishing apparatus that has a rotatable surface plate on the upper face of which abrasive cloth is bonded, and a polishing head provided in a manner opposed to the surface plate and having a wafer holding device. The apparatus performs polishing by pressing the surface of a wafer to the abrasive cloth with the back face of the wafer held on a holding face of the wafer holding device. The polishing method has a polishing step where the surface of the wafer is polished to a total polish margin without changing the polishing apparatus. The method is formed of plural divisional polishing steps that are the divisions of the polishing step, and a holding position of the wafer in late divisional polishing steps is changed to a position different from a holding position in early divisional polishing steps.

(57) **要約:** 本発明は、研磨による面ダレを防止し平坦度の高いウェーハ、特にSOIウェーハの製造ができるウェーハの研磨方法及び装置を提供する。本発明は、上面に研磨布を貼付した回転可能な定盤と、該定盤に相対向して設けられウェーハ保持盤を備えた研磨ヘッドとを有し、該ウェーハ保持盤の保持面にウェー

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